How Pump-Induced Particles Affect Low-k CMP Defectivity

High shear flow generated by positive displacement pumps increases the distribution of oversized particles, leading to significantly increased wafer surface defectivity (scratches or roughness) during CMP, whereas less defectivity was found in slurries circulated by a magnetically levitated (maglev) centrifugal pump.

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Oversized particles in chemical mechanical planarization (CMP) slurries are one of the most important causes of defectivity during CMP of dielectrics and metals. The slurry distribution systems and pumps may play significant roles in increasing the number and distribution of oversized particles. We examined the stress effects and resulting wafer-level defectivity caused by positive displacement pumps and centrifugal pumps during low-k polishing. Excellent correlation between the pump-induced agglomeration effects and defectivity was established. Modeling and testing showed that the average shear stress in a positive displacement pump is ~100× higher than that of a magnetically levitated (maglev) centrifugal pump.

Particle agglomeration under shear flow

CMP slurries that consist of particles and chemicals could be the most critical consumable in the semiconductor industry[1,2]; however, some studies have shown that positive displacement pumps (e.g., bellows and a diaphragm) may generate high shear stress and tend to agglomerate particles during slurry handling.[3-6] Aggregated particles in the slurries not only could reduce the lifetime of filters,[7] but could also cause surface defectivity during the CMP process.[8,9] We must understand the mechanism of pump-induced particle agglomeration to solve this problem.

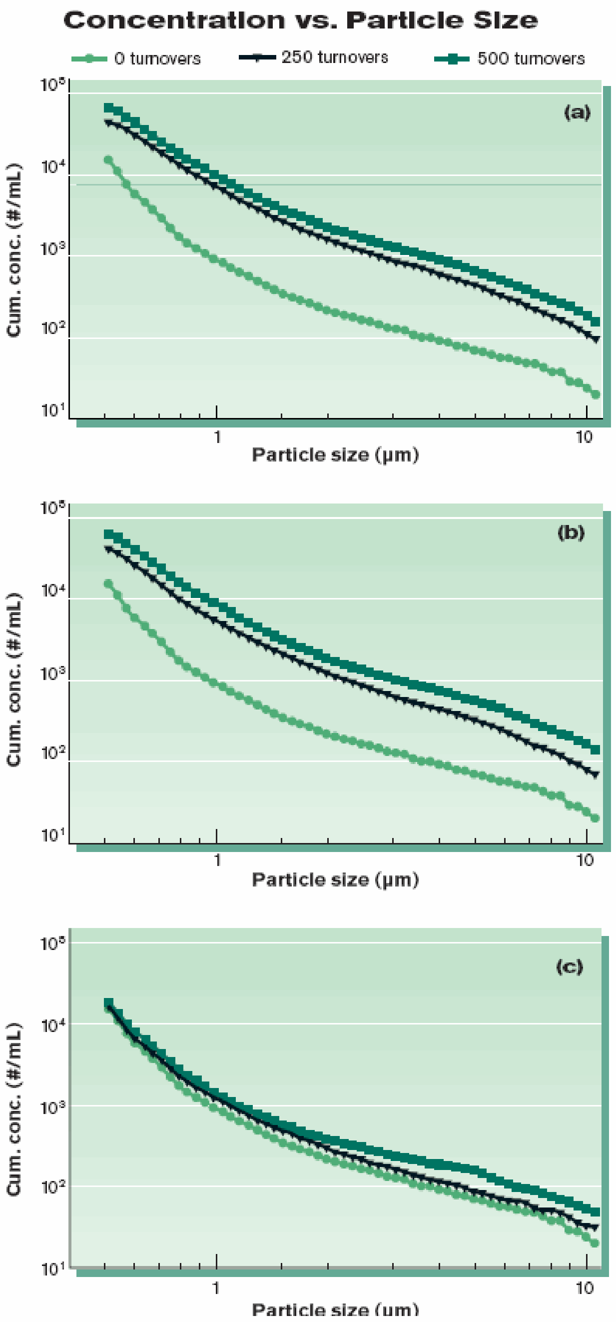
The kinetic theory of rapid aggregation was first worked by von Smoluchowski.[10] His kinetic model assumes that the particle collisions are binary and proportional to particle concentration. The aggregation rate of k-fold aggregates, dNk/dt, is given by the time evolution of the cluster size aggregates, i and j-folds:

$$\frac{dN_k}{dt} = \frac{1}{2}\sum_{i+j=k}^{i=k-1} k_{ij} N_i N_j - N_k \sum_{k=1}^{\infty} k_{ki} N_i \qquad (1)$$

where k_{ij} is the second-order aggregation constant. In this study, high shear flow generated by pumps could be the main cause of particle agglomeration in the slurry delivery. We used the Smoluchowski theory of shear aggregation[10,11] to simulate the process of particle aggregation under shear flow. The aggregation constant, k_{ij}, is a function of shear rate, G, and particle size, a:

$$k_{ij} = \frac{4}{3} G (a_i + a_j) \qquad (2)$$

If we consider the effect of electrostatic interaction between particles in the system, the total electrostatic interaction may provide a potential

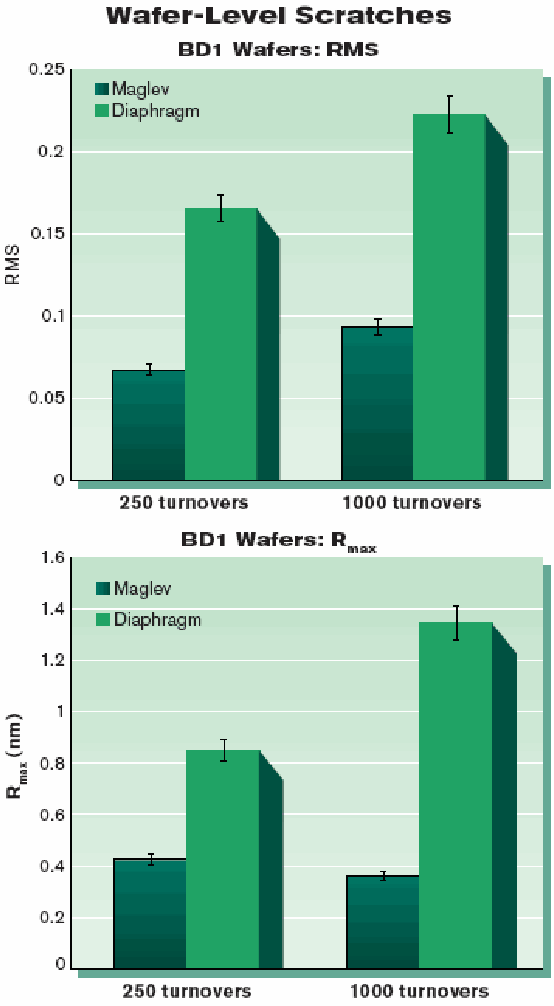


1. The maglev centrifugal pump (c) caused less agglomeration than the bellows (a) or diaphragm pump (b) because of insignificant change in particle tail.

Modeling particle agglomeration

Using the Smoluchowski theory of shear aggregation, this slow aggregation model describes the pump's effect on the evolution of individual aggregates. These aggregate concentrations are influenced by particle types, slurry formulations and external mechanical forces applied on the slurry itself during the slurry handling process. The extent of particle agglomeration depends on the interaction between shear stress and inter-particle forces. These forces play an important role to stabilize the suspensions and are determined by the DLVO theory. The total interaction (Wt) or *W* is given by the balance between the attractive potential (Wa) and repulsive potential (Wr), as shown in Figure 3. We could use the W to predict the efficiency of particle collision and simulate the stress effect on the growth of aggregate concentrations.

First, we simulated the pump's effect on particle agglomeration in low-k slurry to observe the evolution of particle size distributions after 500 turnover times. We took the input values for simulation, such as initial particle size distribution, slurry properties and electrostatic interaction, from the experimental data. Figure 4 shows the particle size distributions of as-received slurry and circulated slurries by pumps. The centrifugal and positive displacement pumps slightly influence the initial particle size distribution, which is not the main reason to increase oversized particles. The key factor to influence oversized particle distribution is its as-received oversized particles content, which collides together, increasing the distribution of oversized particles under the shear flow. Thus, we would like to discuss how shear stress influences the oversized particle distribution.



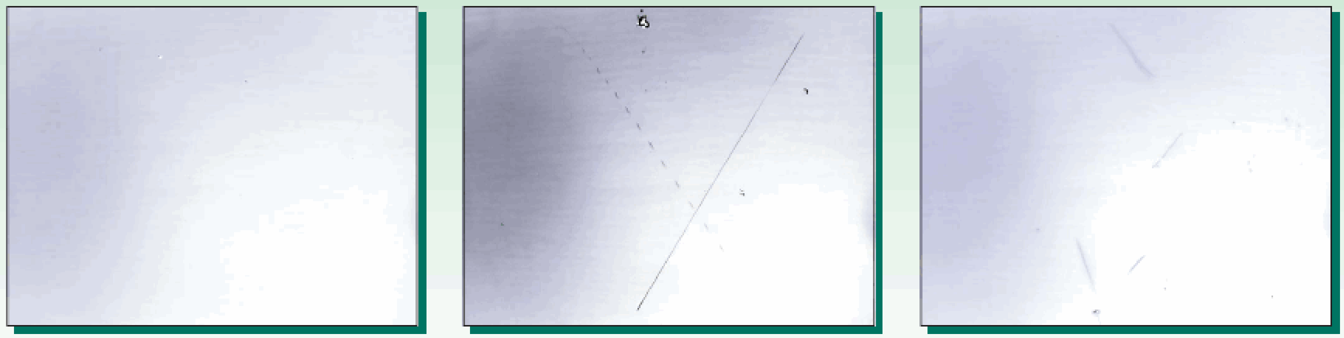
7. Surface defectivity in low-k CMP using circulated slurries from a diaphragm and centrifugal pumps.

Figure 5 shows how shear stress (10^3, 10^5 and 5×10^5 Pa) influences oversized particle distribution in low-k slurries. High shear flow in the slurry caused the particles to approach each other more closely and agglomerate more oversized particles after 500 turnovers. Furthermore, the comparison between simulated data and experimental data can be used to determine the shear stress generated by the pumps (Fig. 6). The simulated data has excellent agreement with the experimental data.

The simulation shows that the shear stress generated in positive displacement pumps is approximately two orders of magnitude higher than maglev pumps.

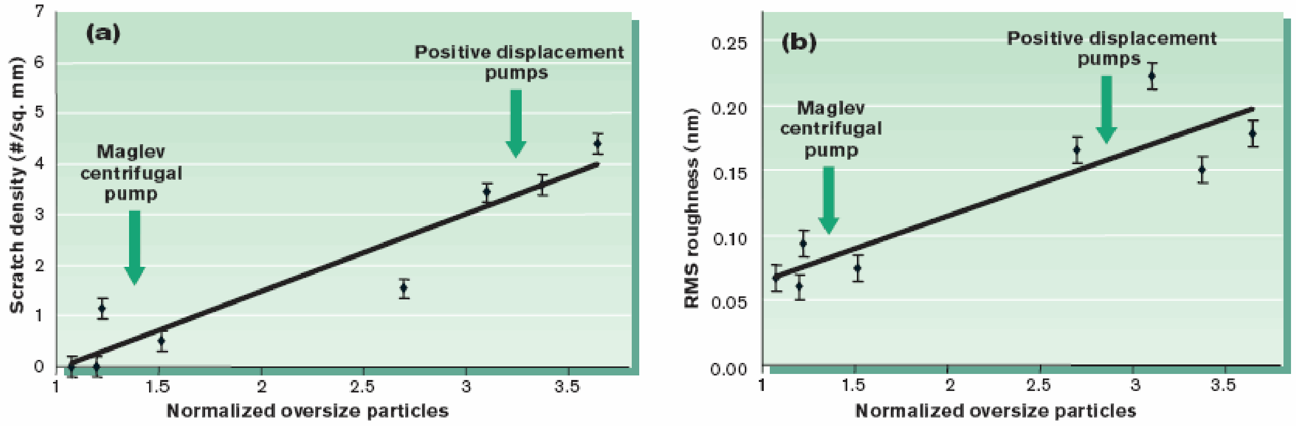
Wafer-level defectivity

Figure 7 compares the surface defectivity of low-k wafers as a function of turnovers for slurries circulated by positive displacement and centrifugal pumps. Oversized particle distribution increased with turnovers and caused increased surface defectivity during CMP. The slurries circulated by positive displacement pumps caused more oversized particles and polished defectivity on low-k wafers than centrifugal pump processed slurries. Thus, the effect of the pump-induced oversized particles on defectivity could be determined by correlation between oversized particles and defect density observed on low-k wafers via optical microscopy (200X). Surface defectivity of polished BD1 wafers showed that circulated slurries of positive displacement pumps caused more micro scratches than circulated slurries of centrifugal pump (Fig. 8). These correlated data (e.g., defect density,



8. Fewer scratches were seen using optical microscopy (200X) for BD1 wafers with low-k slurry delivered by centrifugal pump (a) vs. diaphragm (b) or bellows (c).

Defectivity vs. Normalized Oversized Particles



9. There is excellent correlation between the increase of normalized oversized particles with scratch density and root mean square (RMS) roughness.

root mean square (RMS) and normalized oversized particle numbers) were obtained by varying turnovers and flow rates (Table). Consequently, excellent correlations between the increase of normalized oversized particle with RMS roughness and the scratch density were established (Fig. 9). In both figures, points near the origin correspond to slurries circulated by centrifugal pumps that have less effect of pump-induced particle agglomeration and less defectivity during the polishing. Points far off from the origin correspond to slurries circulated by positive displacement pumps that have more oversized particles and surface defectivity.

Conclusion

Positive displacement pumps (bellows and a diaphragm) cause significant agglomeration (oversized particles) in low-k slurries. The magnitude of pump-induced slurry agglomeration depends on the shear stress and chemical nature of the slurry. The normalized oversized particle distributions show that the maglev centrifugal pump caused less shear flow and did not show any significant particle agglomeration in low-k slurries.

The slow aggregation model demonstrated the stress effect on particle agglomeration and had an excellent agreement with the experimental data. Based on our simulated model and experimental results, the average shear stress in a positive displacement pump is ~100× higher than that of a maglev centrifugal pump. High shear flow generated by positive displacement pumps increased the distribution of oversized particles, leading to significantly increased surface defectivity (scratches or roughness) during CMP, whereas less defectivity was found in slurries circulated by centrifugal pumps. Excellent correlation was established between the roughness/defect density and the degree of agglomeration. **SI**

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